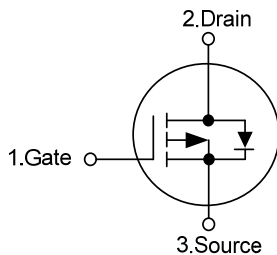


**12P10****Power MOSFET****9.4A, 100V P-CHANNEL
POWER MOSFET****DESCRIPTION**

The **12P10** uses advanced proprietary, planar stripe, DMOS technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable to be used in low voltage applications such as audio amplifier, high efficiency switching DC/DC converters, and DC motor control.

FEATURES

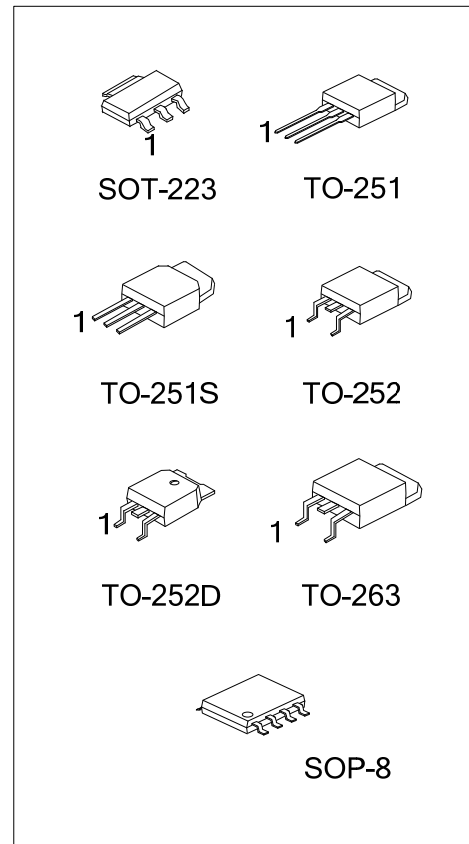
- * $R_{DS(ON)} < 0.29\Omega$ @ $V_{GS} = -10V$
- * Low capacitance
- * Low gate charge
- * Fast switching capability
- * Avalanche energy specified

SYMBOL**ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
12P10L-AA3-R	12P10G-AA3-R	SOT-223	G	D	S	-	-	-	-	-	Tape Reel
12P10L-TM3-T	12P10G-TM3-T	TO-251	G	D	S	-	-	-	-	-	Tube
12P10L-TMS-T	12P10G-TMS-T	TO-251S	G	D	S	-	-	-	-	-	Tube
12P10L-TN3-R	12P10G-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel
12P10L-TND-T	12P10G-TND-T	TO-252D	G	D	S	-	-	-	-	-	Tube
12P10L-TND-R	12P10G-TND-R	TO-252D	G	D	S	-	-	-	-	-	Tape Reel
12P10L-TQ2-R	12P10G-TQ2-R	TO-263	G	D	S	-	-	-	-	-	Tape Reel
12P10L-TQ2-T	12P10G-TQ2-T	TO-263	G	D	S	-	-	-	-	-	Tube
12P10L-S08-T	12P10G-S08-T	SOP-8	S	S	S	G	D	D	D	D	Tube
12P10L-S08-R	12P10G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

	(1) T: Tube, R: Tape Reel
	(2) AA3: SOT-223, TM3: TO-251, TMS: TO-251S TN3: TO-252, TND: TO-252D, TQ2: TO-263, S08: SOP-8
	(3) L: Lead Free, G: Halogen Free



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	-100	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current		I_D	-9.4	A
Pulsed Drain Current (Note 2)		I_{DM}	-37.6	A
Avalanche Current (Note 2)		I_{AR}	-9.4	A
Single Pulsed Avalanche Energy (Note 3)		E_{AS}	370	mJ
Repetitive Avalanche Energy (Note 2)		E_{AR}	5.0	mJ
Power Dissipation	TO-251/TO-251S TO-252/TO-252D	P_D	50	W
	TO-263		65	W
	SOT-223		8	W
	SOP-8		5	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse width limited by $T_{J(MAX)}$

3. $L=6.3\text{mH}$, $I_{AS}=-9.4\text{A}$, $V_{DD}=-25\text{V}$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$

4. $I_{SD}\leq -11.5\text{A}$, $di/dt\leq 300\mu\text{A/s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J=25^{\circ}\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-251/TO-251S TO-252/TO-252D	θ_{JA}	110	$^{\circ}\text{C/W}$
	TO-263		62.5	$^{\circ}\text{C/W}$
	SOT-223		125	$^{\circ}\text{C/W}$
	SOP-8		150	$^{\circ}\text{C/W}$
Junction to Case	TO-251/TO-251S TO-252/TO-252D	θ_{JC}	2.5	$^{\circ}\text{C/W}$
	TO-263		1.9	$^{\circ}\text{C/W}$
	SOT-223		14	$^{\circ}\text{C/W}$
	SOP-8		25	$^{\circ}\text{C/W}$

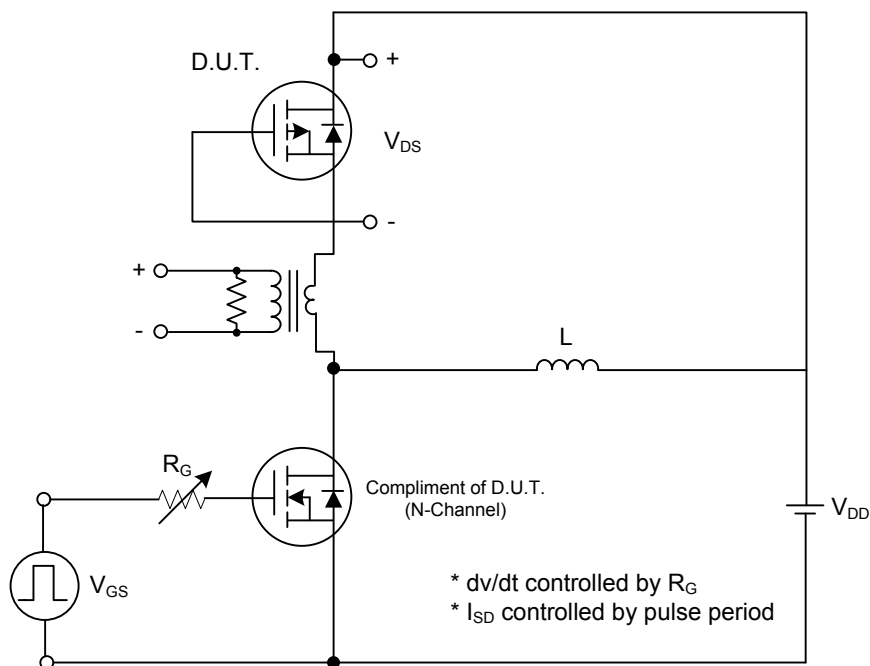
■ **ELECTRICAL CHARACTERISTICS** ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0 V, I _D =-250μA	-100			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V			-1	μA
		V _{DS} =-100V, T _C =125°C			-10	μA
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±30V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =-250μA	-2.0		-4.0	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-4.7A		0.24	0.29	Ω
Forward Transconductance	g _{FS}	V _{DS} =-40V, I _D =-4.7A (Note 1)		6.3		S
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{DS} =-25V, V _{GS} =0V, f=1.0MHz		620	800	pF
Output Capacitance	C _{OSS}			220	290	pF
Reverse Transfer Capacitance	C _{RSS}			65	85	pF
SWITCHING PARAMETERS						
Total Gate Charge	Q _G	V _{DS} =-80V, I _D =-11.5A, V _{GS} =-10V(Note 1, 2)		21	27	nC
Gate Source Charge	Q _{GS}			4.6		nC
Gate Drain Charge	Q _{GD}			11.5		nC
Turn-ON Delay Time	t _{D(ON)}	V _{DD} =-50V, I _D =-11.5A, R _G =25Ω(Note 1, 2)		15	40	ns
Turn-ON Rise Time	t _R			160	330	ns
Turn-OFF Delay Time	t _{D(OFF)}			35	80	ns
Turn-OFF Fall-Time	t _F			60	130	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-9.4A			-4.0	V
Maximum Body-Diode Continuous Current	I _S				-9.4	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				-37.6	A

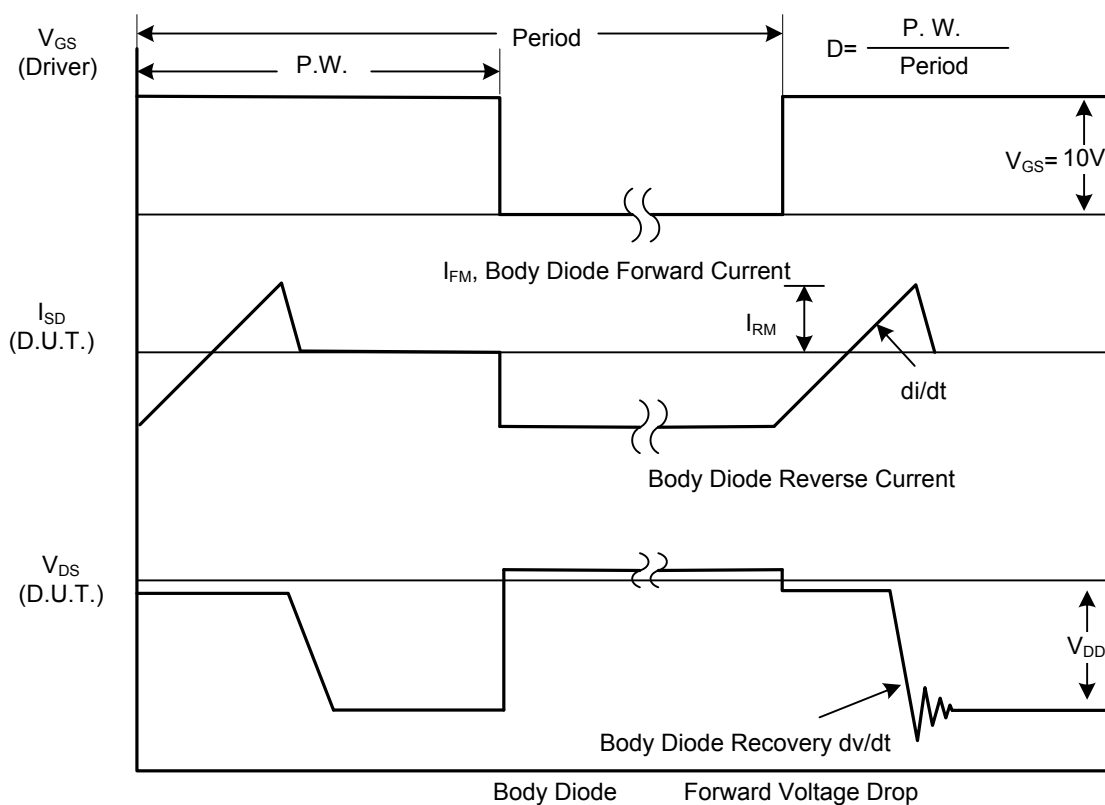
Note: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

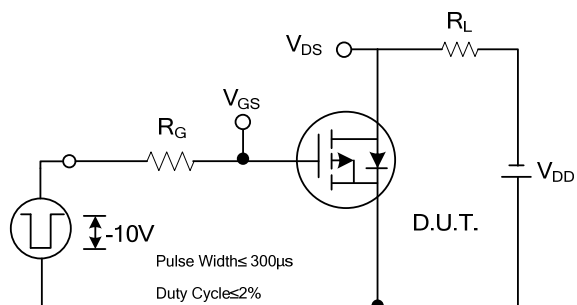


Peak Diode Recovery dv/dt Test Circuit

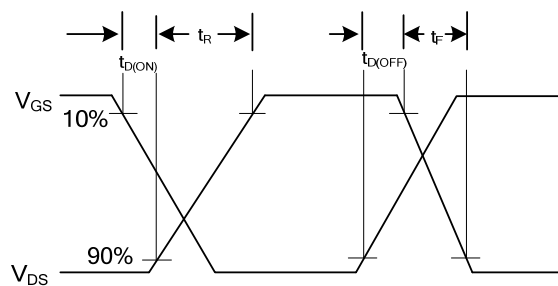


Peak Diode Recovery dv/dt Waveforms

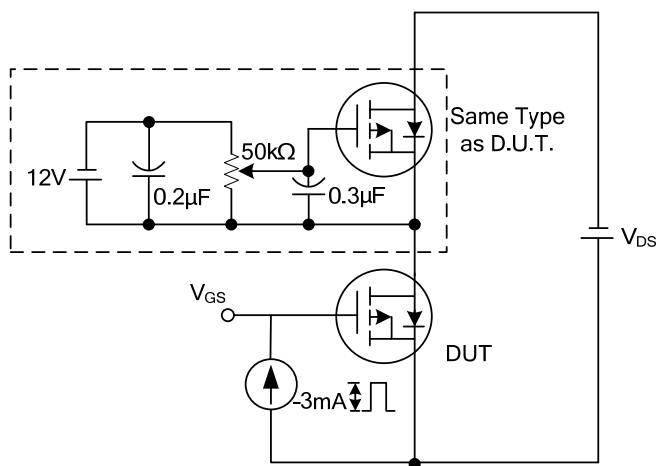
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



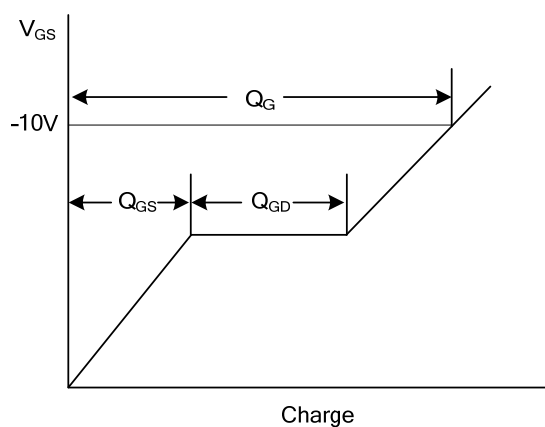
Switching Test Circuit



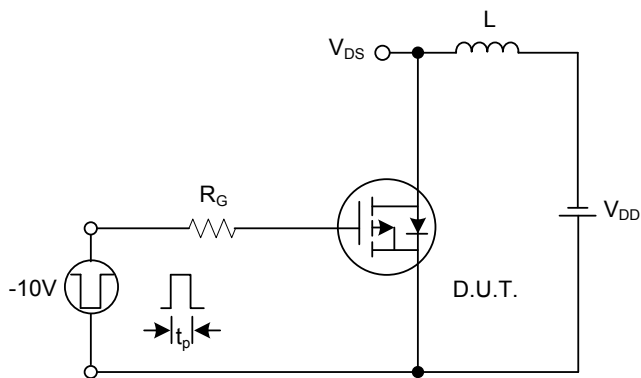
Switching Waveforms



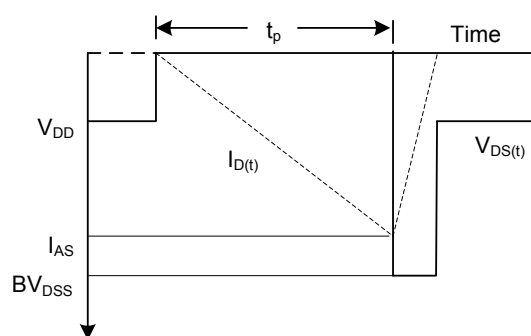
Gate Charge Test Circuit



Gate Charge Waveform

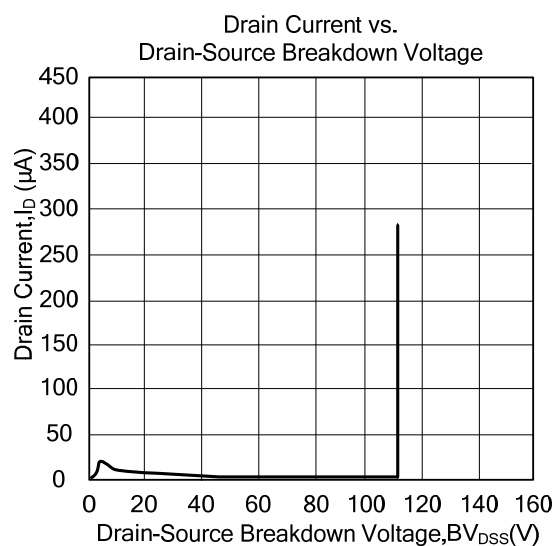
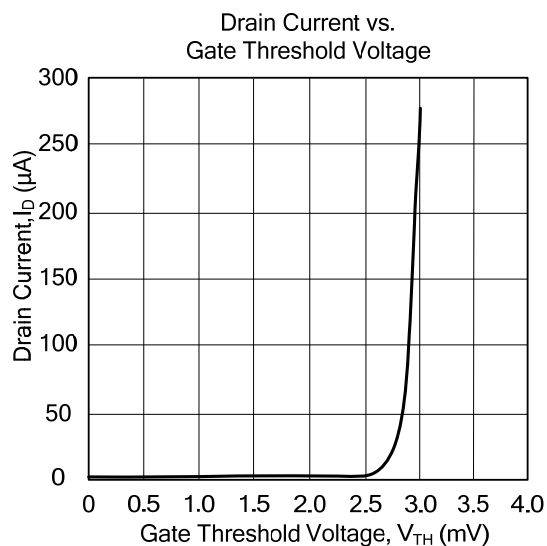
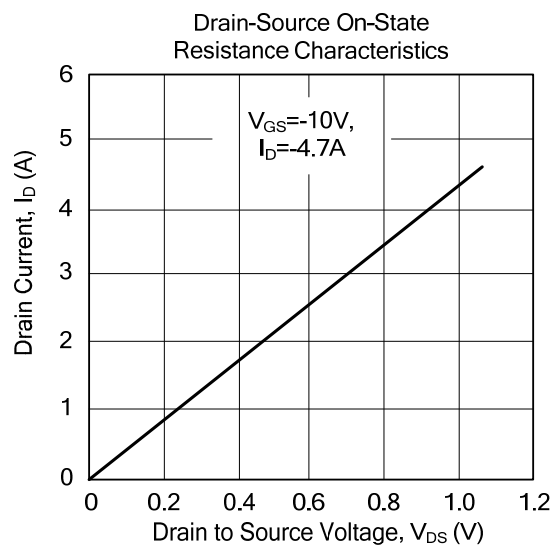
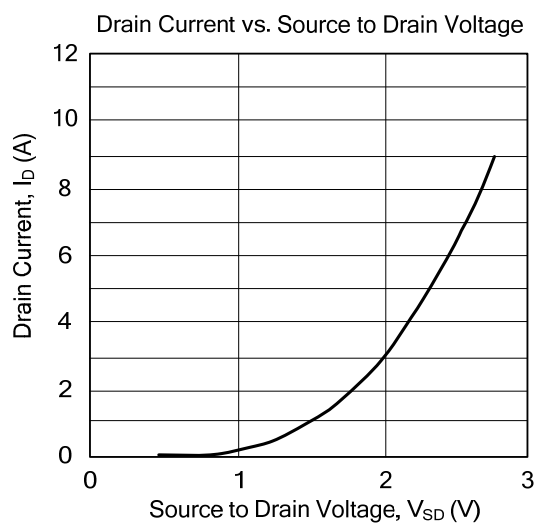


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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